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(54) Title: METHOD OF FORMING DIELECTRIC FILMS WITH REDUCED METAL CONTAMINATION

METAL CONTAMINANT	O3 + Ar	O3 + He	O3 + N2
Cr	4.0	*	1500

All values times: 1x1014 atoms/cm 2

** Indicates measurement was below the detection limit.*

(57) Abstract

A method of forming dielectric layers having reduced metal contamination by Chemical Vapor Deposition (CVD). The CVD system includes an ozone system and a CVD reactor. Oxygen and a nitrogen free dilution gas are introduced into the ozone system where a gas stream including ozone is produced. The gas stream is delivered through metal conduits to the CVD reactor, whereby corrosive vapors which would corrode the conduits are not substantially formed, thereby providing gases which are substantially free of metal contamination which react and deposits layers having reduced metal contamination.